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Electronic Supplementary Information

Three-dimensional Branched SiC Nanowires Field Emitters with Singlecrystal Integrated Structures and Increased Emission Sites: Ultralow

Turn-on Filed and High Stability

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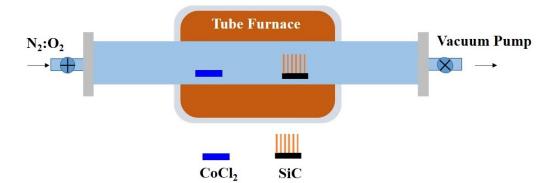


Fig. S1 Schematic diagram of the catalyst was epitaxial grown on SiC backbone nanowires surface by a gas-phase in-situ cation exchange method.

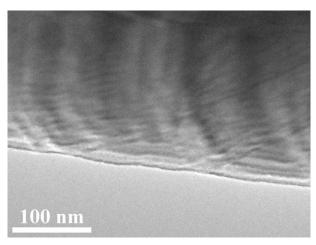
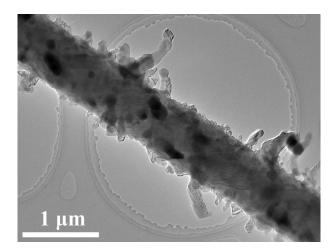


Fig. S2 TEM image of S0 under high magnification.



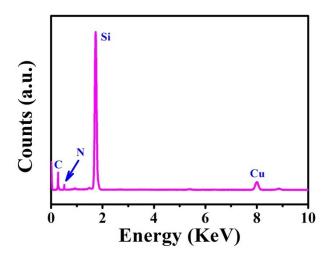


Fig. S4 EDX spectrum recorded from the 3D branched SiC nanowires.